

N-Channel MOSFETs (>500V...900V); Package: PG-TO220-3; VDS (max): 600.0 V;
Package: TO-220; RDS(ON) @ TJ=25°C VGS=10: 99.0 mOhm; ID(max) @ TC=25°C:
31.0 A; IDpuls (max): 93.0 A;

Manufacturers	Infineon Technologies Corporation
Package/Case	TO-220
Product Type	Transistors
RoHS	
Lifecycle	



Images are for reference only

Please submit RFQ for IPP60R099CP or [Email to us: sales@ovaga.com](mailto:sales@ovaga.com) We will contact you in 12 hours.

[RFQ](#)

General Description

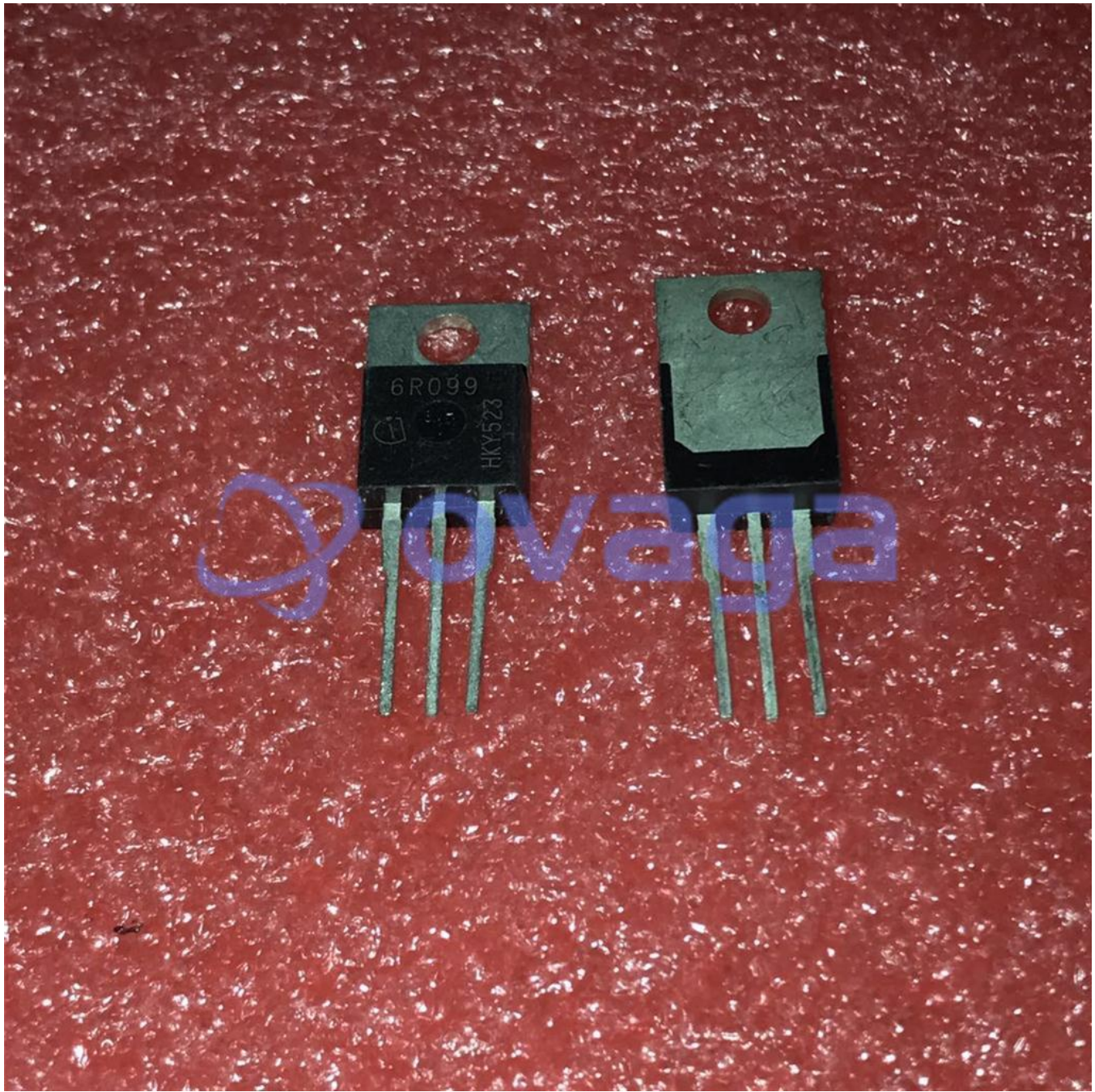
IPP60R099CP is a power MOSFET transistor made by Infineon Technologies.

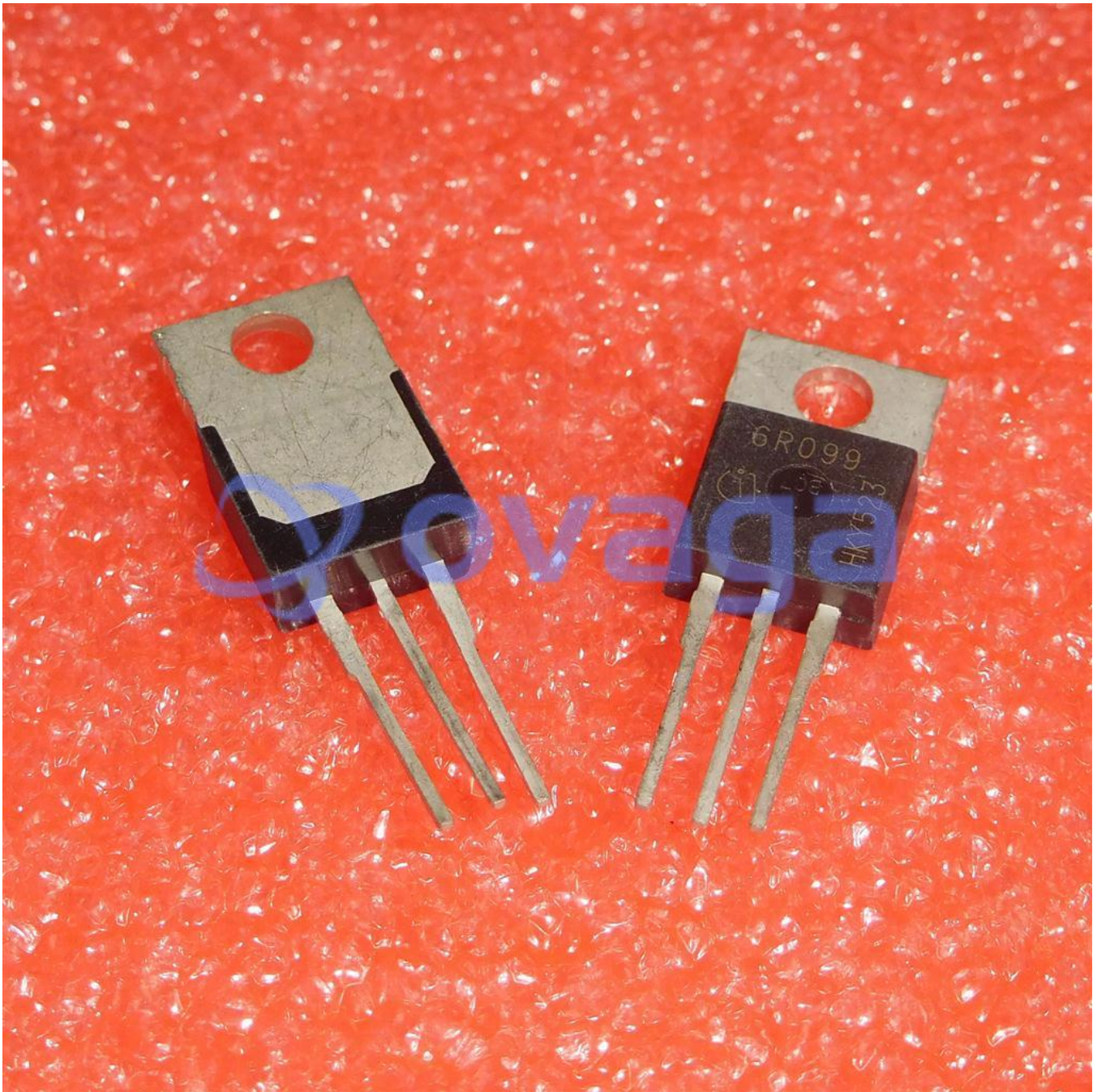
Features

- Drain-source voltage (Vdss) of 600V
- Continuous drain current (Id) of 19A
- Low on-resistance (Rds(on)) of 0.099 Ohms
- Fast switching speed and low gate charge for efficient operation
- TO-220 package for easy mounting

Application

- Power supplies
- Switching regulators
- Motor control
- Lighting applications
- Solar inverters





Related Products



[IPP60R070CFD7](#)

Infineon Technologies Corporation
TO-220-3



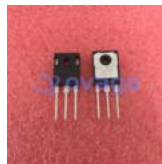
[IPB180N06S4-H1](#)

Infineon Technologies Corporation
PG-TO263-7-3



[IPG20N04S4-12](#)

Infineon Technologies Corporation
TDSON-8



[IPW65R080CFD](#)

Infineon Technologies Corporation
TO-247



[IPD25N06S4L-30](#)

Infineon Technologies Corporation
PG-TO252-3



[IPD180N10N3G](#)

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TO-252



[IPP60R074C6](#)

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TO-220-3



[IPD70R1K4P7S](#)

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TO252-3